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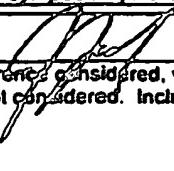
Sheet A1 of 1

		Complete if Known		
		Application Number	10772,882	
		Filing Date	February 5, 2004	
		First Named Inventor	Sander	
		Group Art Unit	2811	
		Examiner Name	Jerome Jackson, Jr.	
		Attorney Docket Number	5308-389	

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
	1. 6,639,255			Inoue et al.	10-28-2003
	2. 6,586,781			Wu et al.	07-01-2003
	3. 6,448,648			Boos	09-10-2002
	4. 6,028,328			Riecher et al.	02-22-2000
	5. 5,948,547			Kim et al.	08-31-1999
	6. 5,885,860			Weitzel et al.	03-23-1999
	7. 5,298,445			Asano	03-28-1994
	8. 5,172,197			Nguyen et al.	12-15-1992
	9. 5,053,348			Mishra et al.	10-01-1991
	10. 4,778,158			Stoneham et al.	11-28-1988
	11. 2004/0056908			Sander et al.	04-01-2004
	12. 2004/0029330			Hussain et al.	02-12-2004
	13. 2004/0021152			Nguyen et al.	02-05-2004
	14. 2003/0020092			Parikh et al.	01-30-2003
	15. 2002/0086908			Smith	04-10-2003 6/2002

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)		
	16. PCT WO 93/23877 A1			Massachusetts Institute of Technology	11-25-1993	
	17. PCT WO 01/57929 A1			Cree Lighting Company	08-09-2001	
	18. JP 10-050982			Nippon Telegraph & Telephone Corp.	02-20-1998	
	19. EP 0 563 847 A2			Matsushita Electric Industrial Co., Ltd.	10-05-1993	

OTHER NON-PATENT LITERATURE DOCUMENTS							
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published					T
		Author	Title of Article	Title of Item	Date	Page(s)	
	20. Breitschadel et al., "Minimization of Leakage Current of Recessed Gate AlGaN/GaN HEMTs by Optimizing the Dry-Etching Process," <i>Journal of Electronic Materials</i> , Vol. 28, No. 12 (1999).						
	21. Burn et al., "Recessed Gate GaN MODFETs," <i>Solid State Electronics</i> , Vol. 41, No. 2, pp. 247-50 (1997)						
	22. Chen et al., "Reactive ion etching for gate recessing of AlGaN/GaN Field-effect transistors," <i>J. Vac. Sci. Technol. B</i> , Vol. 17, No. 6, (1999).						
	23. Egawa et al., "Recessed gate AlGaN/GaN modulation-doped field-effect transistors on sapphire," <i>Applied Physics Letters</i> , Vol. 78, No. 1, pp. 121-23 (2000).						
	24. Heitman et al., "Polarization Effects in AlGaN/GaN and GaN/AlGaN/GaN heterostructures," <i>Journal of Applied Physics</i> , Vol. 93, No. 12, pp. 10114-118 (2003).						
	25. Heitman, Sten J., <i>MOCVD Growth Technologies for Applications in AlGaN/GaN High Electron Mobility Transistors</i> , Dissertation, University of California—Santa Barbara, 190 pages (2002).						
	26. Karmalkar et al., "Enhancement of Breakdown Voltage in AlGaN/GaN High Electron Mobility Transistors Using a Field Plate," <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 8 (2001).						
	27. Karmalkar et al., "RESURF AlGaN/GaN HEMT for High Voltage Power Switching," <i>IEEE Electron Device Letters</i> , Vol. 22, No. 8, pp. 373-75 (2001).						
	28. Kuzmit et al., "Annealing of Schottky contacts deposited on dry etched AlGaN/GaN," <i>Semiconductor Science and Technology</i> , Vol. 17, No. 11 (2002).						
	29. Neuburger et al., "Design of GaN-based Field Effect Transistor Structures based on Doping Screening of Polarization Fields," WA 1.5, 7 th Wide-Bandgap III-Nitride Workshop, March 2002.						
	30. Sriram et al., "RF Performance of AlGaN/GaN MODFET's on High Resistivity SiC Substrates," Presentation at Materials Research Society Fall Symposium, 1997.						
	31. Sriram et al., "SiC and GaN Wide Bandgap Microwave Power Transistors," <i>IEEE Semiconductors Symposium</i> , March 18, 1998.						

Examiner Signature  Date Considered 

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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